
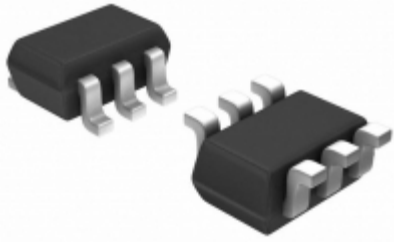






	<p><b>SI1988DH-T1-GE3</b></p>
	<p><b>Hersteller-Teilenummer:</b> <a href="#">SI1988DH-T1-GE3</a></p> <p><b>Hersteller / Marke:</b> <a href="#">Vishay / Siliconix</a></p> <p><b>Teil der Beschreibung:</b> MOSFET 2N-CH 20V 1.3A SC-70-6</p> <p><b>Datenblätter:</b>  <a href="#">SI1988DH-T1-GE3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 15868 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI1988DH-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET 2N-CH 20V 1.3A SC-70-6
Kategorie	<a href="#">Diskrete Halbleiterprodukte</a> > <a href="#">Transistoren-FETs</a> ,
Teilstatus	15868 pcs Stock
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	1.25W
Verpackung / Gehäuse	6-TSSOP, SC-88, SOT-363
Supplier Device-Gehäuse	SC-70-6 (SOT-363)
Typ FET	2 N-Channel (Dual)
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	1.3A
Rds On (Max) @ Id, Vgs	168 mOhm @ 1.4A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	4.1nC @ 8V
Eingabekapazität (Ciss) (Max) @ Vds	110pF @ 10V
Verpackung	Tape & Reel (TR)







SI1988DH-T1-GE3 ist neu im Original, Suche SI1988DH-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1988DH-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI1988DH-T1-GE3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>SI1972DH-T1-E3</b> Vishay / Siliconix MOSFET 2N-CH 30V 1.3A SC70-6</p>	 <p><b>SI1983DT-285-T1-E3</b> Vishay Precision Group SI1983DT-285-T1-E3 VISHAY</p>	 <p><b>SI1972DH-T1-GE</b> VISHAY SI1972DH-T1-GE VISHAY</p>	 <p><b>SI1988DH-T1-E3</b> Electro-Films (EFI) / Vishay MOSFET 2N-CH 20V 1.3A SC70-6</p>
 <p><b>SI1972DH-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET 2N-CH 30V 1.3A SC-70-6</p>	 <p><b>SI1972DH-T1-GE3</b> Vishay / Siliconix MOSFET 2N-CH 30V 1.3A SC-70-6</p>	 <p><b>SI1973DH-E3</b> VISHAY SI1973DH-E3 VISHAY</p>	 <p><b>SI19993CTG100</b> SILICON SILICON QFP</p>

heiße Teile

Mehr

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|--|--|--|---|--|
|  SI1905DL-T1      |  SI1905DL-T1-E3   |  SI1905DL-T1-E3   |  SI1905DL-T1-GE3    |  SI1906DL-T1      |
|  SI1912EDH        |  SI1912EDH-T1     |  SI1912EDH-T1-E3  |  SI1912EDH-T1-E3    |  SI1912EDH-T1-GE3 |
|  SI1913DH-T1-E3   |  SI1913DH-T1-E3   |  SI1913DH-T1-GE3  |  SI1913EDH-T1       |  SI1913EDH-T1-E3  |
|  SI1913EDH-T1-E3  |  SI1913EDH-T1-GE3 |  SI1917EDH-T1     |  SI1917EDH-T1-E3    |  SI1917EDH-T1-E3  |
|  SI1917EDH-T1-GE3 |  SI1922EDH-T1-GE3 |  SI1922EDH-T1-GE3 |  SI1926DL-T1-E3     |  SI1926DL-T1-E3   |
|  SI1926DL-T1-GE3  |  SI1926DL-T1-GE3  |  SI1958DH-T1-E3   |  SI1958DH-T1-E3     |  SI1965DH-E3      |
|  SI1965DH-T1-E3   |  SI1965DH-T1-E3   |  SI1965DH-T1-GE3  |  SI1965DH-T1-GE3    |  SI1967DH-T1-E3   |
|  SI1967DH-T1-E3   |  SI1967DH-T1-GE3  |  SI1967DH-T1-GE3  |  SI1969DH-E3        |  SI1970DH-T1-GE3  |
|  SI1970DH-T1-GE3  |  SI1972DH-T1      |  SI1972DH-T1-E3   |  SI1972DH-T1-E3     |  SI1972DH-T1-GE   |
|  SI1972DH-T1-GE3  |  SI1972DH-T1-GE3  |  SI1973DH-E3      |  SI1983DT-285-T1-E3 |  SI1988DH-T1-GE3  |

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